	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	1	(transistor) near25 (emitter near3 landing near3 pad)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/02 18:48	
2	BRS	L2	0	(intrinsic near base) near25 (emitter near3 landing near3 pad)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/02 18:49	
3	BRS	L3	0	(intrinsic near base) near25 (landing near3 pad)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/02 19:20	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
4	BRS	L4	20	(intrinsic near base) near25 (landing or pad)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 2 18:49	
5	BRS	L5	3	(intrinsic near base) near25 (emitter) near3 ((landing or pad))	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 2 18:50	
6	BRS	L6	5	(intrinsic) near25 (emitter) near3 ((landing or pad))	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/11/0 2 18:51	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
7	BRS	L7	590	(base) near25 (emitter) near3 ((landing or pad))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/02 18:51	
8	BRS	L9	5	(base) near25 (distan$3) near15 (emitter) near3 ((landing or pad)) near15 (transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/02 18:52	
9	BRS	L8	334	(base) near25 (emitter) near3 ((landing or pad)) near15 (transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/02 18:53	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
10	BRS	L10	2663	(intrinsic near base)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/02 19:21	
11	BRS	L11	1452	(intrinsic near base) near15 (emitter)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/02 19:21	
12	BRS	L12	546	(intrinsic near base) near15 (emitter) near15 (transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/02 19:22	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
13	BRS	L13	0	(intrinsic near base) near15 (emitter near5 pad) near15 (transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/02 19:22	
14	BRS	L14	0	(intrinsic near base) near15 (emitter near5 land$3) near15 (transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/02 19:22	
15	BRS	L15	15	(intrinsic near base) near15 (distan$3) near15 (emitter) near15 (transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/02 19:22	

	U	1	Document ID	Title	Current OR	Pages
1	☐	☐	US 20040211978 A1	Semiconductor device and method of producing same	257/197	17
2	☐	☐	US 5889319 A	RF power package with a dual ground	257/691	6
3	☐	☐	JP 63232364 A	SEMICONDUCTOR DEVICE		4
4	☒	☐	JP 2004172503 A	High pressure resistant power transistor for switching power supply, has multi emitter portions whose sizes are reduced as distance from multi emitter portions and base contact to emitter pad increases		7
5	☒	☐	JP 06120238 A	Overcurrent cut=off switching power transistor for telephone - has multi-base region formed so that resistant between base and emitter contacts is reduced with distance from emitter pad NoAbstract		5

	Issue Date	Current XRef	Retrieval Classif	Inventor	S	C	P
1	20041028			Kobayashi, Junichiro	⊠	☐	☐
2	19990330	257/706; 257/717; 257/732; 257/774		Moller, Thomas W. et al.	⊠	☐	☐
3	19880928	257/552		HAIJIMA, MIKIO et al.	⊠	☐	☐
4	20040617				☐	☐	☐
5	19940428				☐	☐	☐